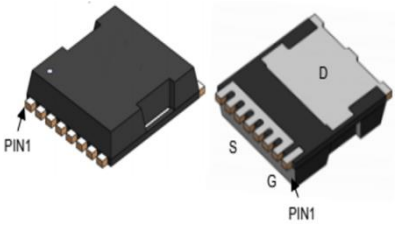
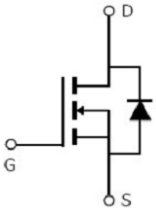
Main Product Characteristics:

V_{DSS}	100V
R_{DS}(on)	1.8mΩ (typ.)
I_D	224A



TOLL



Schematic Diagram

Features and Benefits:

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150℃ operating temperature

Description:

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute Max Rating:

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V ①	224	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V ①	141	
I_{DM}	Pulsed Drain Current ②	896	
P_D @T_C = 25°C	Power Dissipation ③	208	W
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy @ L=0.5mH	795	mJ
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

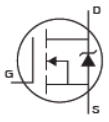
Thermal Resistance

Symbol	Characterizes	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case ③	—	0.6	℃/W
$R_{\theta JA}$	Junction-to-ambient (t ≤ 10s)④	—	62	℃/W

Electrical Characteristics @T_A=25℃ unless otherwise specified

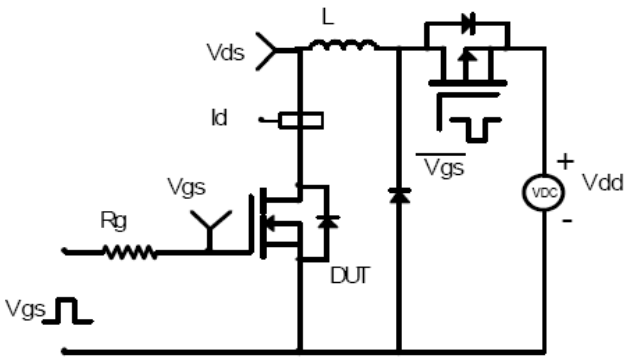
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	100	—	—	V	V_{GS} = 0V, I_D = 250μA
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	1.8	3	mΩ	V_{GS}=10V,I_D = 50A
$V_{GS(th)}$	Gate threshold voltage	2	—	4	V	V_{DS} = V_{GS}, I_D = 250μA
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	V_{DS} = 100V,V_{GS} = 0V
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V_{GS} =20V
		—	—	-100		V_{GS} = -20V
C_{iss}	Input capacitance	—	6209	—	pF	V_{GS} = 0V
C_{oss}	Output capacitance	—	2570	—		V_{DS} = 50V
C_{rss}	Reverse transfer capacitance	—	67	—		f = 100kHz
Q_g	Total gate charge	—	106	—	nC	I_D = 100A,
Q_{gs}	Gate-to-Source charge	—	41	—		V_{DS}=50V,
Q_{gd}	Gate-to-Drain("Miller") charge	—	30	—		V_{GS} = 10V
$t_{d(on)}$	Turn-on delay time	—	39	—	ns	V_{GS}=10V, V_{DD} =50V, R_{GEN}=2.2Ω, R_L =1Ω
t_r	Rise time	—	15	—		
$t_{d(off)}$	Turn-Off delay time	—	50	—		
t_f	Fall time	—	16	—		

Source-Drain Ratings and Characteristics

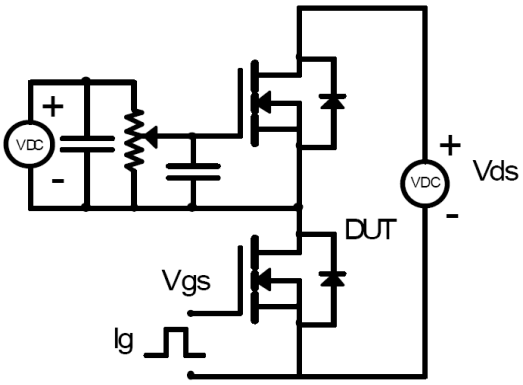
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	224	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	896	A	
V_{sd}	Diode Forward Voltage	—	—	1.2	V	I_S=50A, V_{GS}=0V
t_{rr}	Reverse Recovery Time	—	75	—	ns	V_R=50V,I_F=50A, di/dt= 100A/μs
Q_{rr}	Reverse Recovery Charge	—	123	—	nC	

Test Circuits and Waveforms

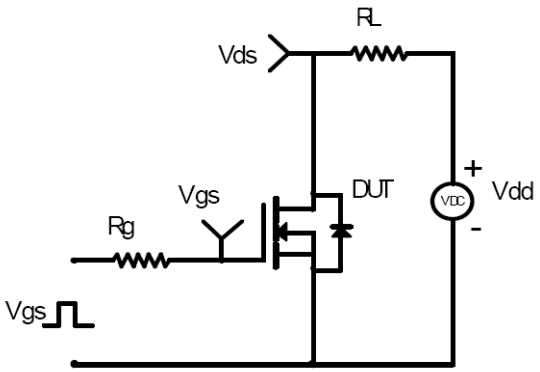
EAS Test Circuit:



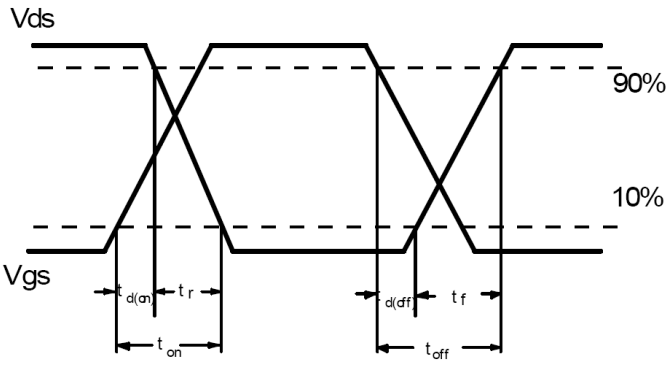
Gate Charge Test Circuit:



Switching Time Test Circuit:



Switching Waveforms:



Notes:

①Calculated continuous current based on maximum allowable junction temperature.

②Repetitive rating; pulse width limited by max. junction temperature.

③The power dissipation P_D is based on max. junction temperature, using junction-to-case thermal resistance.

④The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C

Typical Electrical and Thermal Characteristics

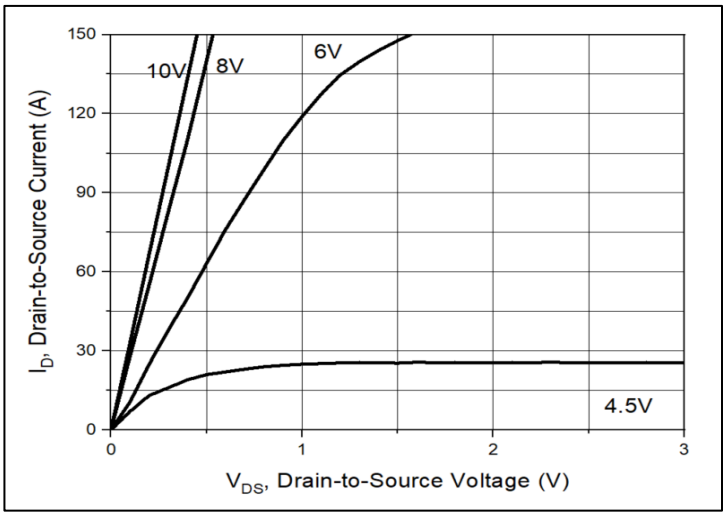


Figure1.Typical Output Characteristics

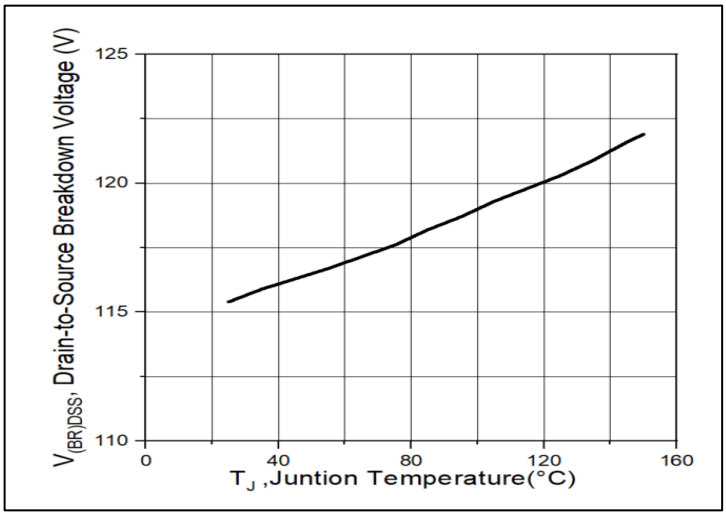


Figure2. Drain-to-Source Breakdown Voltage vs. Junction Temperature

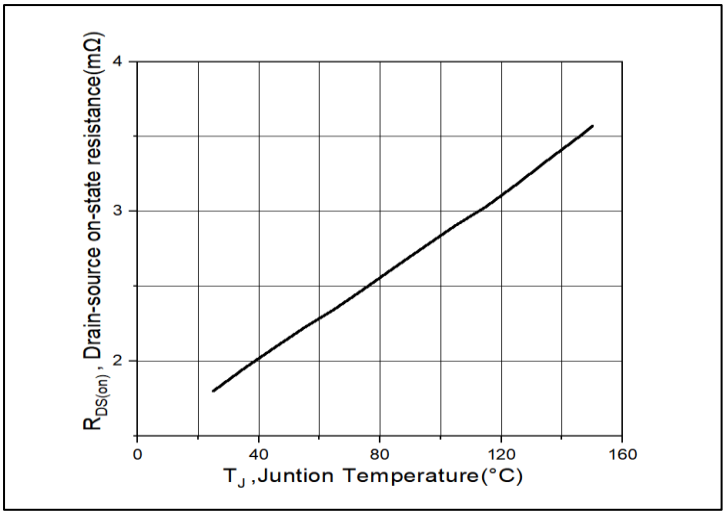


Figure3. $R_{DS(on)}$ vs. Junction Temperature

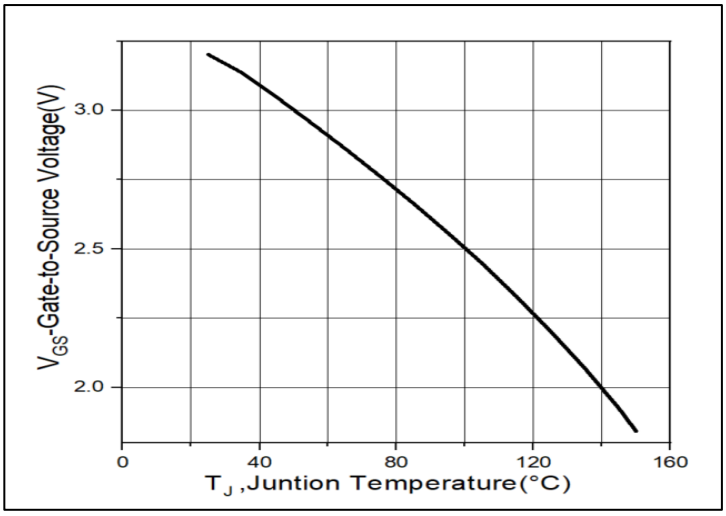


Figure4. Vth vs. Junction Temperature

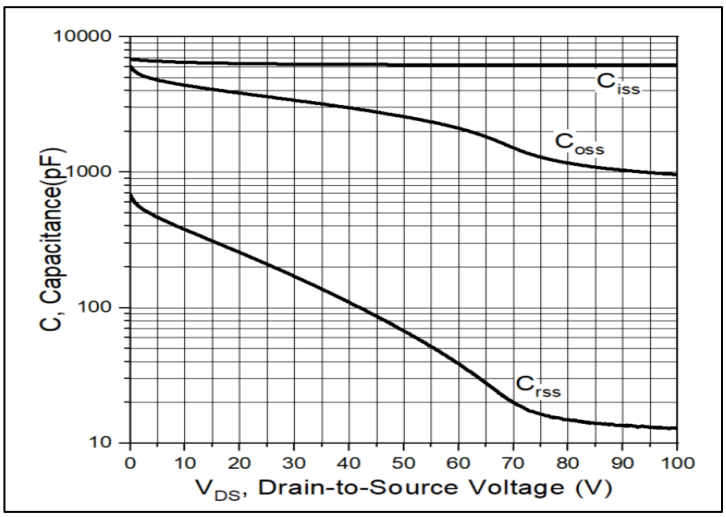


Figure5. Capacitance

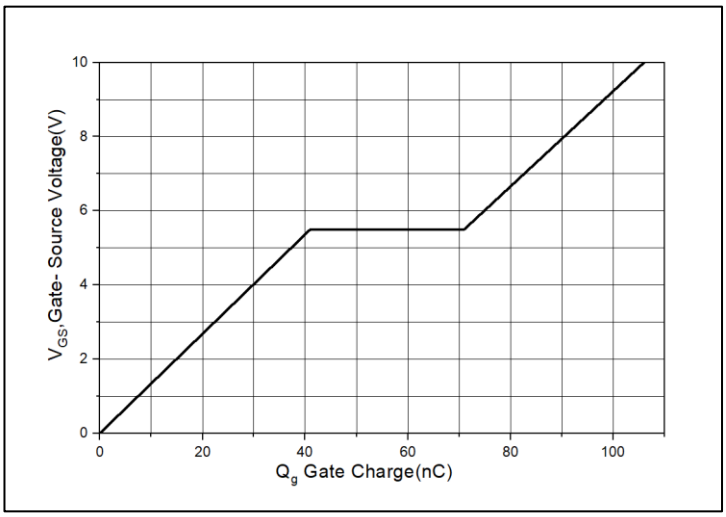


Figure6. Gate Charge

Typical Electrical and Thermal Characteristics

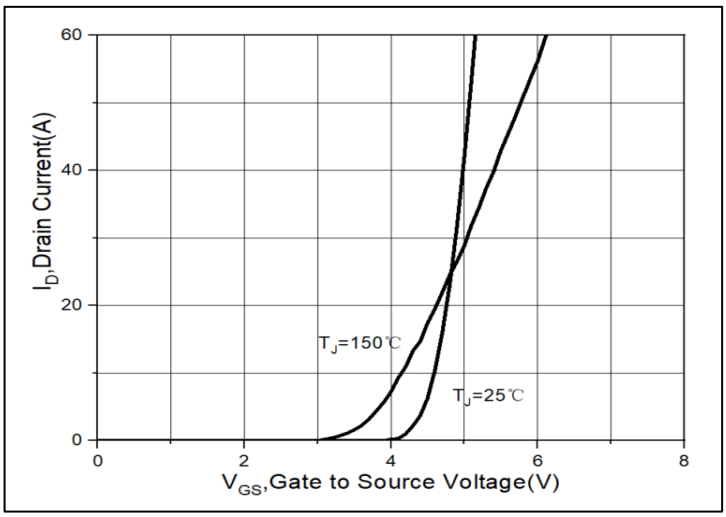


Figure7. Transfer Characteristics

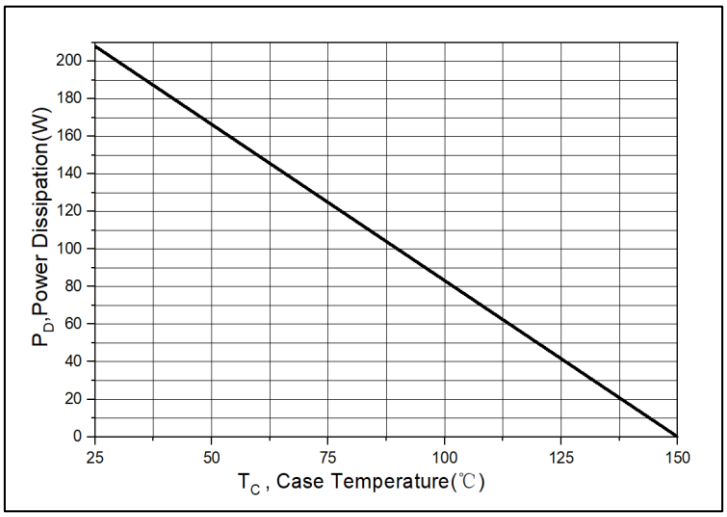
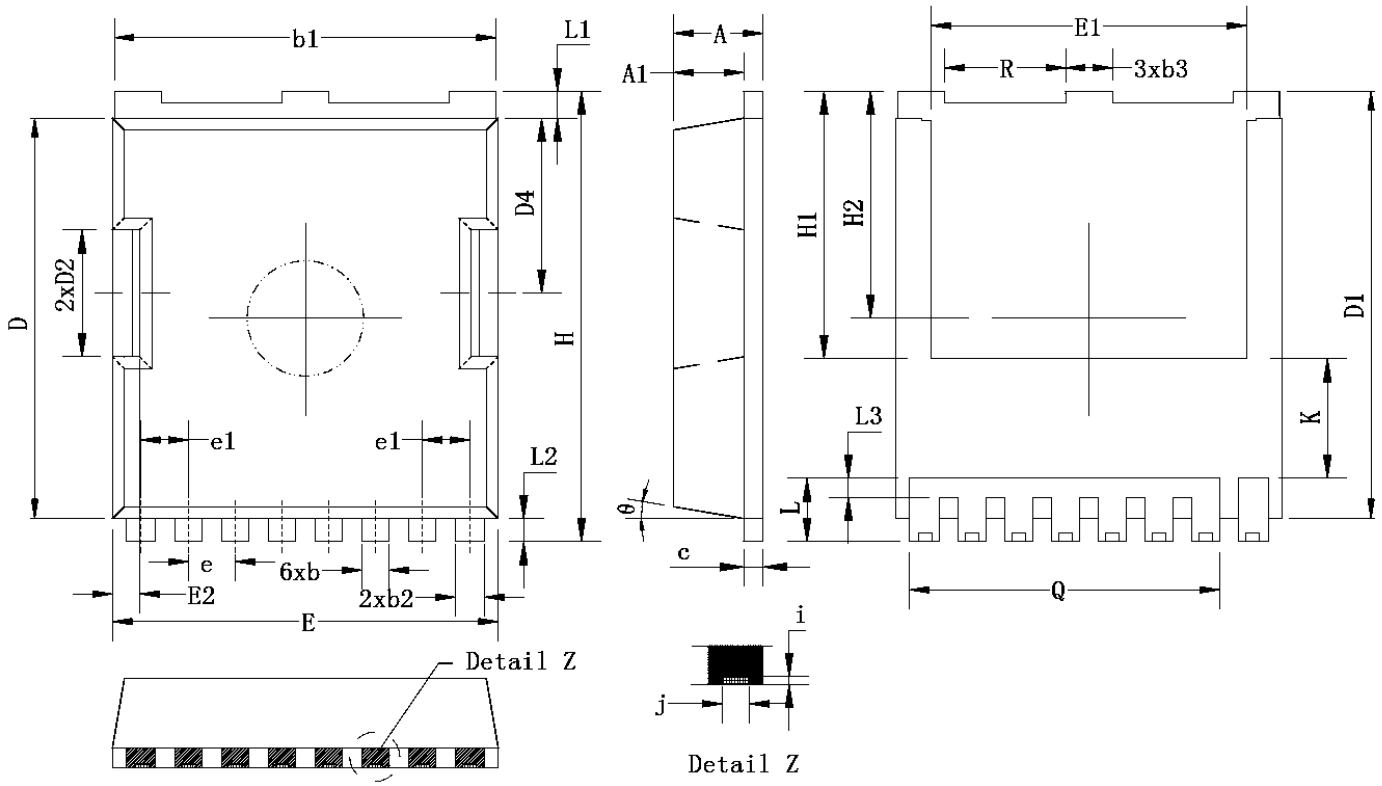


Figure8. Power Dissipation

Mechanical Data：



Symbol	Min	Typ	Max		Symbol	Min	Typ	Max
A	2.25	2.30	2.35		E2	0.65	0.70	0.75
A1	1.75	1.80	1.85		H	11.60	11.70	11.80
b	0.65	0.70	0.75		H1	6.95 BSC		
b1	9.75	9.80	9.85		H2	5.90 BSC		
b2	0.70	0.75	0.80		i	0.10 REF		
b3	1.15	1.20	1.25		j	0.35 REF		
c	0.45	0.50	0.55		K	3.10 REF		
D	10.35	10.40	10.45		L	1.55	1.65	1.75
D1	11.00	11.10	11.20		L1	0.65	0.70	0.75
D2	3.25	3.30	3.35		L2	0.50	0.60	0.70
D4	4.50	4.55	4.60		L3	0.40	0.50	0.60
e	1.20 BSC				Q	7.95 REF		
e1	1.225 BSC				R	3.05	3.10	3.15
E	9.85	9.90	9.95		θ	10°REF		
E1	8.00	8.10	8.20					

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